Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document  Country Code <sup>3</sup> Number <sup>4</sup> Kind Code <sup>5</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T°
₽₩	11	PCT/US 03/34377 /	09-28-2004	PCT International Search Report		
ì	12	DE 4113354 A1	10-29-1992	Siemens AG		
	13	EP 0561672 A1 /	09-22-1993	Commissariat A L'energie Atomique		
	14	EP 0482630 A1 /	04-29-1992	Sumitomo Electric Industries, Ltd.		
	15	GB 2373628 A 🗸	09-25-2002	Queen Mary & Westfield College		
	16	JP 62-120090 /	06-01-1987	Aoki		

08-13-2002

09-24-2002

02-11-2003

US-

US-

US-

6,433,922 B1

6,456,425 B1

6,519,082 B2

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Ghera et al.

Foursa et al.

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Signature	m	10/4/01

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Complete if Known Substitute for Form 1449/PTO **Application Number** 10/659,009 INFORMATION DISCLOSURE Filing Date September 10, 2003 STATEMENT BY APPLICANT First Named Inventor. Remus Nicolaescu et al. (use as many sheets as necessary) 2828 Art Unit 2874 **Examiner Name** Unknown **Attorney Docket Number** 42P17104 **Sheet** of 2 NON PATENT LITERATURE DOCUMENTS T<sup>2</sup> Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the Examiner Cite Initials\* No<sup>1</sup> item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published CLAPS, R. et al., "Stimulated Raman Scattering in Silicon Waveguides", ELECTRONICS DW 17 LETTERS, Vol. 38, No. 22, 24 October 2002. / CLAPS, R. et al., "Observation of Raman Emission in Silicon Waveguides at 1.54µm", 18 OPTICS EXPRESS, Vo. 10, No. 22, 4 November 2002, pp. 1305-1313. CLAPS, R. et al., "Observation of Stimulated Raman Amplification in Silicon Waveguides", 19 OPTICS EXPRESS, Vol. 11, No. 15, 28 July 2003, pp. 1731-1739. RALSTON, J. M. et al., "Spontaneous-Raman-Scattering Efficiency and Stimulated 20 Scattering in Silicon", Physical Review B, Vol. 2, No. 6, 15 September 1970, pp. 1858-1862. SAITO, T. et al., "Spontaneous Raman Scattering In [100], [110], and [11-2] Directional GaP 21 / Waveguides", Journal of Applied Physics, Vol. 90, No. 4, 15 August 2001, pp. 1831-1835. SAITO, T. et al., "Raman Gain and Optical Loss in AlGaP Waveguides", Journal of Applied 22 Physics, Vol. 87, No. 7, 1 April 2000, pp. 3399-3403. SUTO, K. et al., "Semiconductor Raman Amplifier for Terahertz Bandwidth Optical 23 Communication", Journal of Lightwave Technology, Vol. 20, No. 4, April 2002, pp. 705-711. TANG, C.K. et al., "Development of a Library of Low-Loss Silicon-On-Insulator Optoelectronic Devices", IEEE PROCEEDINGS: OPTOELECTRONICS, Vol. 143, No. 5, 24 October 1996, pp. 312-315.

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